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	Autore	Stallinga Peter <1966->
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Sommario/riassunto	Think like an electron Organic electronic materials have many applications and potential in low-cost electronics such as electronic barcodes and in light emitting devices, due to their easily tailored properties. While the chemical aspects and characterization have been widely studied, characterization of the electrical properties has been neglected, and classic textbook modeling has been applied. This is most striking in the analysis of thin-film transistors (TFTs) using thick "bulk" transistor (MOS-FET) descriptions. At first glance the TFTs appear to behave as regular MOS-FETs.